

Supplementary Information for

Doping-induced carrier profiles in organic semiconductors determined from capacitive extraction-current transients

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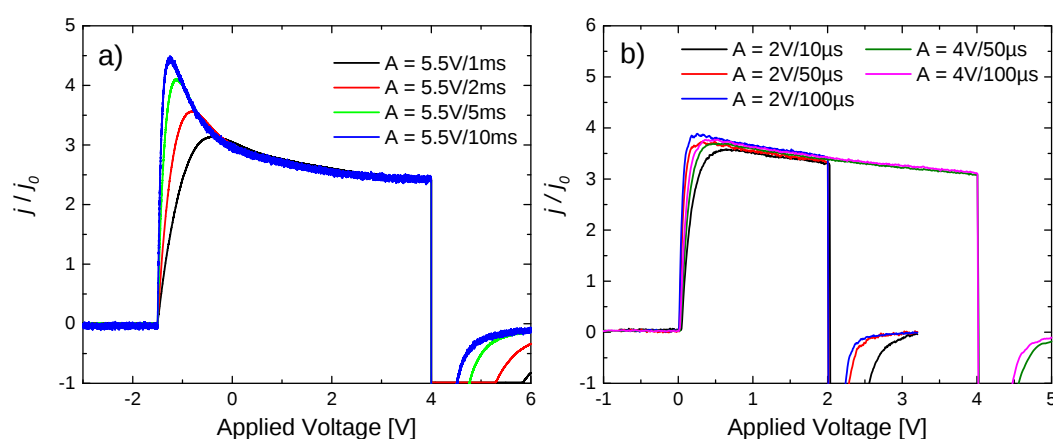


Figure S1. Extraction current transients with varying voltage slopes A for a) a BF-DPB:C₆₀F₃₆ devices with two layers of different dopant concentrations; in the lower doped layer ($d = 40$ nm) the C₆₀F₃₆ to BF-DPB weight ratio is 0.2 % and 4 wt% in the more heavily doped layer ($d = 70$ nm) b) a doped ITO/P3HT/Al device with 0.2 wt % dopants.

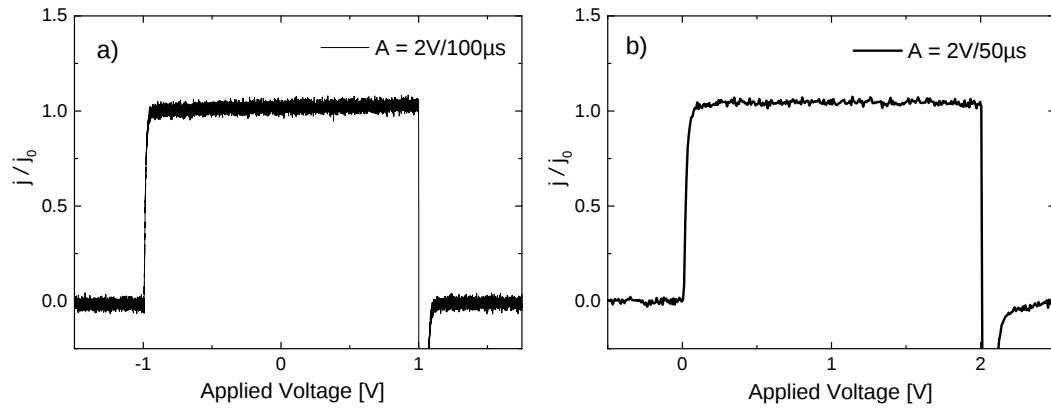


Figure S2. Extraction current transients of a) an undoped of ITO/BF-DPB/LiF/Al device and b) an undoped ITO/P3HT/Al device. Only the geometric capacitive response, j_0 , is seen since no free charges are present in the undoped active layer.